

December 2013

# FCP4N60

# N-Channel SuperFET® MOSFET **600 V, 3.9 A, 1.2** Ω

## **Features**

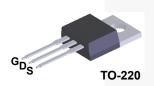
- 650 V @ T<sub>J</sub> = 150°C
- Typ.  $R_{DS(on)}$  = 1.0  $\Omega$
- Ultra Low Gate Charge (Typ. Q<sub>g</sub> = 12.8 nC)
- Low Effective Output Capacitance (Typ. C<sub>oss(eff.)</sub> = 32 pF)
- 100% Avalanche Tested
- · RoHS Compliant

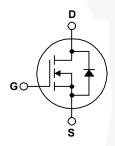
# **Application**

- · LCD / LED / PDP TV and Monitor Lighting
- · Solar Inverter
- · AC-DC Power Supply

# Description

SuperFET® MOSFET is Fairchild Semiconductor's first generation of high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low onresistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switching performance, dv/dt rate and higher avalanche energy. Consequently, SuperFET MOSFET is very suitable for the switching power applications such as PFC, server/telecom power, FPD TV power, ATX power and industrial power applications.





# MOSFET Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter		FCP4N60	Unit
V <sub>DSS</sub>	Drain-Source Voltage		600	V
I <sub>D</sub>	Drain Current - Continuous ( $T_C = 25^{\circ}C$ ) - Continuous ( $T_C = 100^{\circ}C$ )		3.9 2.5	A A
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	11.7	А
V <sub>GSS</sub>	Gate-Source voltage		± 30	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note		128	mJ
I <sub>AR</sub>	Avalanche Current		3.9	Α
E <sub>AR</sub>	Repetitive Avalanche Energy		5.0	mJ
dv/dt	Peak Diode Recovery dv/dt (N		4.5	V/ns
P <sub>D</sub>	Power Dissipation (T <sub>C</sub> = 25°C) - Derate Above 25°C	1.0	50 0.4	W W/°C
T <sub>J,</sub> T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +150	°C
T <sub>L</sub>	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds.		300	°C

# **Thermal Characteristics**

Symbol	Parameter	FCP4N60	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	2.5	2.5 °C/W	
	Thermal Resistance, Junction to Ambient, Max.	83	*C/ <b>V</b> V	

# **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FCP4N60	FCP4N60	TO-220	Tube	N/A	N/A	50 units

# **Electrical Characteristics** T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Off Charac	teristics			I		
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250  \mu\text{A}, T_J = 25^{\circ}\text{C}$				V
		$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}, T_J = 150^{\circ}\text{C}$		650		V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C		0.6		V/°C
BV <sub>DS</sub>	Drain-Source Avalanche Breakdown Voltage	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 3.9 A		700		V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 600 V, V <sub>GS</sub> = 0 V V <sub>DS</sub> = 480 V, T <sub>C</sub> = 125°C			1 10	μA μA
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -30 V, V <sub>DS</sub> = 0 V			-100	nA
On Charac	teristics			I.		
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.0		5.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 2.0 A		1.0	1.2	Ω
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 40 V, I <sub>D</sub> = 2.0 A	\	3.2		S
Dynamic C	Characteristics			I.		
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V,		415	540	pF
C <sub>oss</sub>	Output Capacitance	f = 1.0 MHz		210	275	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			19.5		pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> = 480 V, V <sub>GS</sub> = 0 V, f = 1.0 MHz		12	16	pF
C <sub>oss</sub> eff.	Effective Output Capacitance	V <sub>DS</sub> = 0 V to 400 V, V <sub>GS</sub> = 0 V		32		pF
Switching	Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DD} = 300 \text{ V}, I_D = 3.9 \text{ A}$ $R_G = 25 \Omega$		16	45	ns
t <sub>r</sub>	Turn-On Rise Time			45	100	ns
t <sub>d(off)</sub>	Turn-Off Delay Time			36	85	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)		30	70	ns
Qg	Total Gate Charge	V <sub>DS</sub> = 480 V, I <sub>D</sub> = 3.9 A		12.8	16.6	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 10 V		2.4		nC
Q <sub>gd</sub>	Gate-Drain Charge	(Note 4)		7.1		nC
Drain-Soul	rce Diode Characteristics and Maximur	n Ratings	.,		7/15	110
I <sub>S</sub>	Maximum Continuous Drain-Source Dio	de Forward Current			3.9	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode F	orward Current			11.7	Α
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = 3.9 \text{ A}$			1.4	V
t <sub>rr</sub>	Reverse Recovery Time	$V_{GS} = 0 \text{ V, } I_S = 3.9 \text{ A}$ $dI_F/dt = 100 \text{ A/}\mu\text{s}$		277		ns
Q <sub>rr</sub>	Reverse Recovery Charge			2.07		μС

### Notes

<sup>1.</sup> Repetitive rating: pulse-width limited by maximum junction temperature.

<sup>2.</sup> I $_{AS}$  = 1.9 A, V $_{DD}$  = 50 V, R $_{G}$  = 25  $\Omega$ , starting T $_{J}$  = 25°C.

 $<sup>3.~</sup>I_{SD} \leq 3.9~A,~di/dt \leq 200~A/\mu s,~V_{DD} \leq BV_{DSS},~starting~T_J = 25^{\circ}C.$ 

<sup>4.</sup> Essentially independent of operating temperature typical characteristics.

# **Typical Performance Characteristics**

Figure 1. On-Region Characteristics

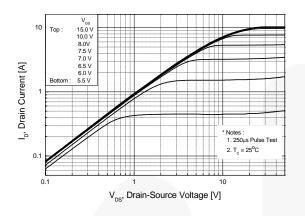


Figure 2. Transfer Characteristics

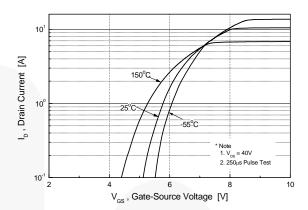


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

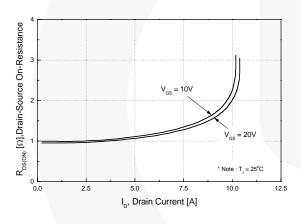
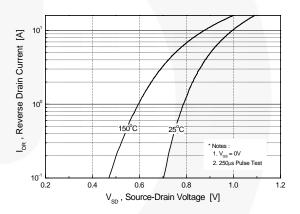
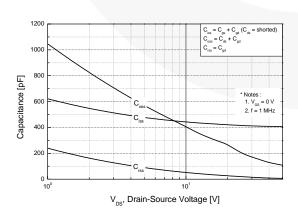


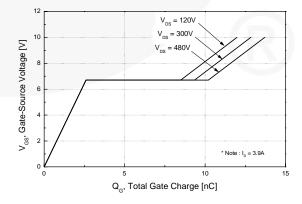
Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue



**Figure 5. Capacitance Characteristics** 



**Figure 6. Gate Charge Characteristics** 



# **Typical Performance Characteristics** (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

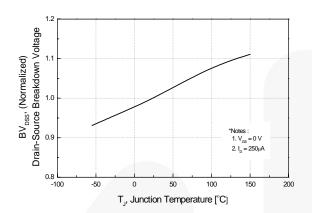


Figure 8. On-Resistance Variation vs. Temperature

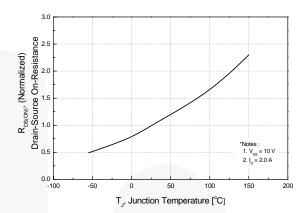


Figure 9. Maximum Safe Operating Area

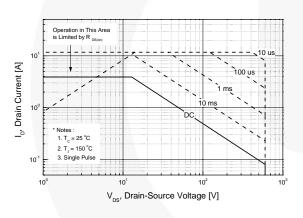


Figure 10. Maximum Drain Current vs. Case Temperature

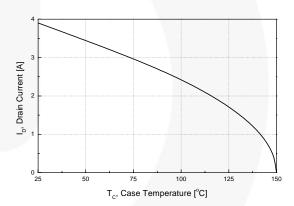
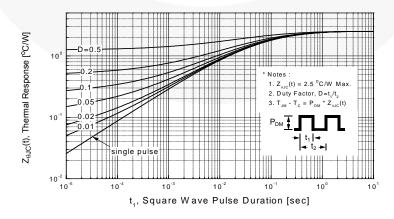


Figure 11. Transient Thermal Response Curve



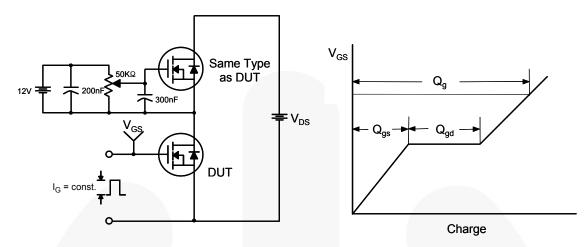


Figure 12. Gate Charge Test Circuit & Waveform

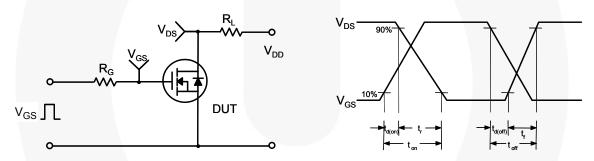


Figure 13. Resistive Switching Test Circuit & Waveforms

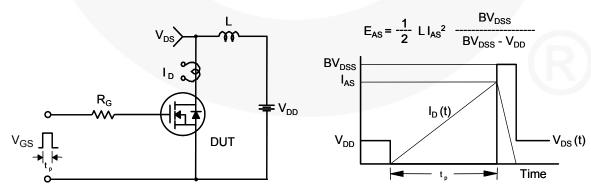


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

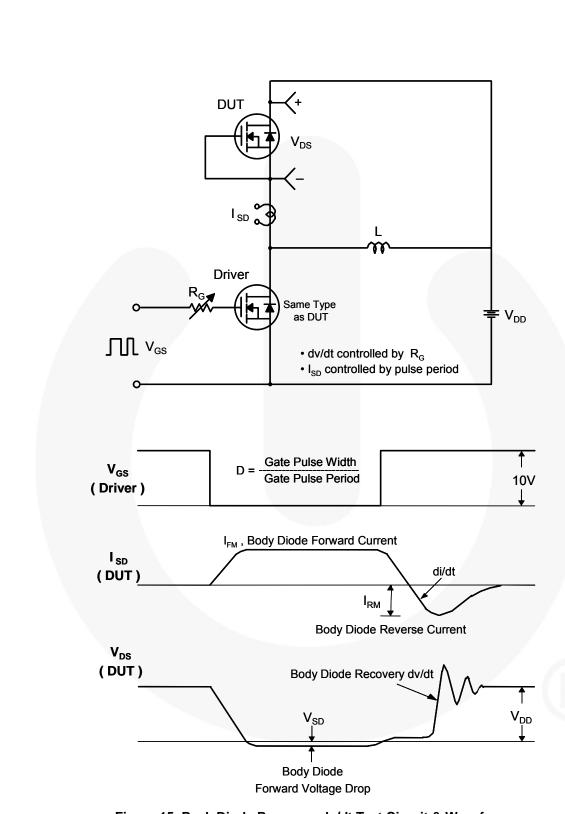


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

# **Mechanical Dimensions**

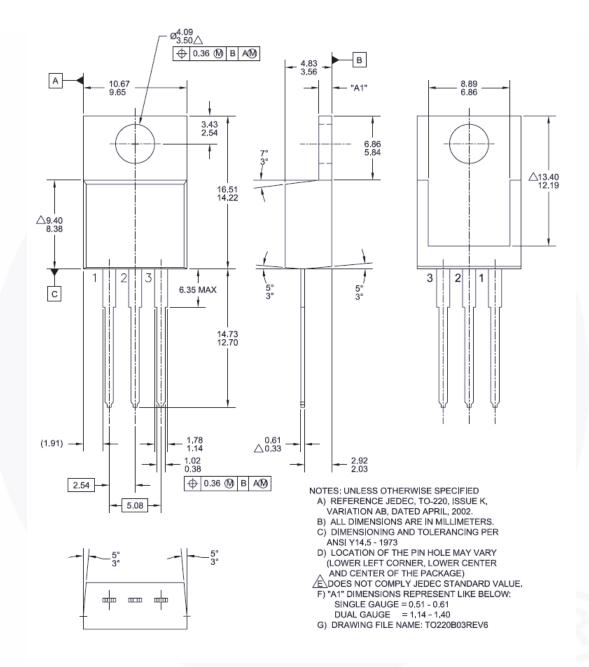


Figure 16. TO-220, Molded, 3-Lead, Jedec Variation AB

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